

<b>PTO-1449</b>  <b>Information Disclosure Citation</b> <b>in an Application</b>		Application No. <b>09/864,714</b>		Applicant(s) <b>Ajit P. Paranjpe et al.</b>	
Docket Number <b>021208.0238</b>		Group Art Unit <b>2814</b>		Filing Date <b>May 23, 2001</b>	

  

U.S. PATENT DOCUMENTS

DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
B.	6174377	1/16/2001	Doering et al.	118	729	1/4/99
C.	5879459	3/09/1999	Gadgil et al.	118	715	8/29/97
D.	5916365	6/29/1999	Sherman	117	92	8/16/96
E.	6015590	1/18/2000	Suntola et al.	427	255.23	09/25/96
F.	6200893	3/13/2001	Sneh	438	685	3/11/99
G.	6342277	1/29/2002	Sherman	427	562	4/14/99
H.	2002/0041931	4/11/2002	Suntola et al.	427	255.28	5/14/01
I.	6387185	5/14/2002	Doering et al.	118	729	1/16/01
J.	6391785	5/21/2002	Satta et al.	438	704	8/23/00
K.	6416577	7/9/2002	Suntola et al.	117	88	06/07/00
L.	2002/0106846	8/8/2002	Seutter et al.	438	200	2/2/01
M.	2002/0108570	8/15/2002	Lindfors	118	715	4/16/01
N.	6447607	9/10/2002	Soininen et al.	117	200	12/27/00
O.	6451119*	9/17/2002	Sneh et al.	118	715	11/29/00
P.	6451695	9/17/2002	Sneh	438	685	12/22/00
Q.	6464779	10/15/2002	Powell et al.	117	89	1/19/01
R.	6475910	11/5/2002	Sneh	438	685	9/22/00
S.	6475276	11/5/2002	Elers et al.	117	84	10/13/00
T.	6482262	11/19/2002	Elers et al.	117	84	10/13/00
	6482740	11/19/2002	Soininen et al.	438	686	5/15/01

  

FOREIGN PATENT DOCUMENTS

DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES    NO	
U.	62221102	09/29/1987	JP (with English abstract)	H01F	41/14	X
V.	WO 00/38191	06/29/2000	PCT	G11C	11/15	X

  

NON-PATENT DOCUMENTS - DOCUMENT (Including Author, Title, Source, and Pertinent Pages)

W.	Addison, C.C. et al. "The Vapour Pressure of Anhydrous Copper Nitrate, and its Molecular Weight in the Vapour State", <i>J. Chem. Soc.</i> , pp. 3099-3106	1958
X.	Akerman, J.J et al., "Identifying Tunneling in Ferromagnetic-Insulator-Ferromagnetic Thin Film Structures", World-wide web, physics.ucsd.edu/kuksgrp/Tunneling.html, pp. 1-6,	Printed 02/04/2002
Y.	Bobo, J.F. et al., "Spin-dependent Tunneling Junctions with Hard Magnetic layer Pinning", <i>Journal of Applied Physics</i> , vol. 83, No. 11, pp. 6685-6687	1998
Z.	Daughton, J.M., World-wide web nve.com/otherbiz/mram2.pdf, "Advanced MRAM Concepts", pp. 1-6	02/07/2001

  

EXAMINER	DATE CONSIDERED
	2/16/06

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

<b>PTO-1449</b> <div style="border: 1px solid black; border-radius: 50%; width: 100px; height: 100px; display: flex; align-items: center; justify-content: center; margin: 10px auto;"> <div style="writing-mode: vertical-rl; transform: rotate(180deg); font-weight: bold;">OIP</div> <div style="text-align: center;"> <b>Information Disclosure Citation</b>  <b>in an Application</b>  <b>NOV 30 2005</b> </div> </div>		<b>Application No.</b> <b>09/864,714</b>		<b>Applicant(s)</b> <b>Ajit P. Paranjpe et al.</b>	
<b>Docket Number</b> <b>021208.0238</b>		<b>Group Art Unit</b> <b>2814</b>		<b>Filing Date</b> <b>May 23, 2001</b>	

  

U.S. PATENT DOCUMENTS							
	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
21	A.	2002/0187084	12/12/2002	Lindfors et al.	422	177	7/24/02
	B.	6503330	1/7/2003	Sneh et al.	118	715	12/22/99
	C.	6506352	1/14/2003	Lindfors et al.	423	240	7/20/00
	D.	6511539	1/28/2003	Raajmakers	117	102	9/8/99
	E.	6524952	2/25/2003	Srinivas et al.	438	649	6/20/00
	F.	6540838	4/1/2003	Sneh et al.	118	715	6/28/02
	G.	6548424	4/15/2003	Putkonen	438	785	4/16/01
	H.	6551406	4/22/2003	Kilpi	118	728	12/27/00
	I.	6562140	5/13/2003	Bondestam et al.	118	715	5/10/00
	J.	2003/0098468	5/22/2003	Solinen et al.	438	200	11/19/02
	K.	6572705	6/3/2003	Suntola et al.	118	702	1/14/00
	L.	2003/0101927	6/5/2003	Raajmakers	117	200	12/10/02
	M.	6578374	6/17/2003	Bondestam et al.	118	725	1/25/01
	N.	2003/0121469	7/3/2003	Lindfors et al.	117	105	10/11/02
	O.	6599572	7/29/2003	Saani et al.	427	249.18	1/18/01
	P.	2003/0140854	7/31/2003	Kilpi	118	715	2/13/03
	Q.	6602784	8/5/2003	Sneh	438	680	8/6/02
	R.	2003/0150385	8/14/2003	Bondestam et al.	118	722	3/6/03
	S.	6616986	9/9/2003	Sherman	427	562	10/9/01
	T.	6620723	9/16/2003	Byun et al.	438	627	6/27/00
51	U.	6627268	9/30/2003	Fair et al.	427	533	5/3/01

  

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
21	V.	WO 02/09126	01/31/2002	PCT	H01F	10/32	X
51	W.	W 02/09158	01/31/2002	PCT	H01L	21/00	X

  

NON-PATENT DOCUMENTS - DOCUMENT (Including Author, Title, Source, and Pertinent Pages)			
21	X.	Fereday, R.J. et al., "Anhydrous Cobalt (III) Nitrate", <i>Chemical Communications</i> , pp. 271	1968
1	Y.	Hsiao, R., "Fabrication of Magnetic Recording Heads and Dry Etching Head Materials", <i>IBM Journal of Research and Development</i> , vol. 43, (1/2):1999, pp. 89-102	1999
51	Z.	Imai, Takuji, World-wide web <a href="http://nikkeibp.asiabiztech.com/nea/200008/tech_108675.html">nikkeibp.asiabiztech.com/nea/200008/tech_108675.html</a> , "100 Gbit/Inch HDD Just Around the Corner", pp. 1-6	08/2000

  

<b>EXAMINER</b> 	<b>DATE CONSIDERED</b> <div style="text-align: center; font-size: 1.5em;">2/16/02</div>
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PTO-1449

Application No.

Applicant(s)

Information Disclosure Citation  
in an Application

09/864,714

Ajit P. Paranjpe et al.

Docket Number

Group Art Unit

Filing Date

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May 23, 2001

## U.S. PATENT DOCUMENTS

	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
A	2003/0183171	10/2/2003	Sneh et al.	118	724	3/27/03
B	6630401	10/7/2003	Sneh	438	680	8/8/02
C	6630030	10/7/2003	Suntola et al.	118	728	1/4/00
D	6632279	10/14/2003	Ritala et al.	117	101	10/13/00
E	6635985	10/21/2003	Lee et al.	257	758	10/9/01
F	6638862	10/28/2003	Sneh	438	685	8/8/02
G	6638859	10/28/2003	Sneh et al.	438	680	9/27/02
H	6638810	10/28/2003	Bakli et al.	438	240	11/5/01
I	6652924	11/25/2003	Sherman	427	576	5/24/01
J	6660126	12/9/2003	Nguyen et al.	156	345.34	3/2/01
K	6664192	12/18/2003	Satta et al.	438	704	4/15/02
L	2004/0005753	1/8/2004	Kostamo et al.	438	222	3/20/03
M	2004/0007171	1/15/2004	Ritala et al.	117	89	7/10/03
N	6679951	1/20/2004	Soininen et al.	148	240	11/13/01
O	6689210	2/10/2004	Soininen et al.	117	89	7/24/02
P	6720260	4/13/2004	Fair et al.	438	680	6/20/03
Q	2004/0076837	4/22/2004	Hein et al.	428	446	10/22/02
R	2004/0076751	4/22/2004	Sherman	427	255.34	10/10/03
S	6727169	4/27/2004	Raaijmakers et al.	438	622	8/23/00
T	2004/0083949	5/6/2004	Sherman	117	84	10/22/03
U	6734020	5/11/2004	Lu et al.	436	55	3/7/01
V	2004/0121616	6/24/2004	Satta et al.	438	778	12/8/03
W	6759081	7/6/2004	Huganen et al.	427	58	4/30/02
X	2004/0130029	7/8/2004	Raaijmakers et al.	257	758	12/15/03

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO
Y	WO 01/88972	11/22/2001	PCT	H01L	21/321	X

## NON-PATENT DOCUMENTS - DOCUMENT (Including Author, Title, Source, and Pertinent Pages)

Z	Nilsen, O et al, "Thin Film Deposition of lanthanum Manganite Perovskite by the ALE Process", <i>Journal of Materials Chemistry</i> , vol. 9, pp. 1781-1784.	1999
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EXAMINER

DATE CONSIDERED

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<b>PTO-1449</b> <b>Information Disclosure Citation</b> <b>in an Application</b> <b>NOV 30 2005</b>		Application No.		Applicant(s)	
		09/864,714		Ajit P. Paranjpe et al.	
		Docket Number		Group Art Unit	Filing Date
		021208.0238		2814	May 23, 2001

  

U.S. PATENT DOCUMENTS							
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<input checked="" type="checkbox"/>	A.	6764546	7/20/2004	Raaijmakers	117	93	12/10/02
<input type="checkbox"/>	B.	6767582	7/27/2004	Elers	427	253	10/12/00
<input type="checkbox"/>	C.	6777353	8/17/2004	Putkonen	438	785	4/8/03
<input type="checkbox"/>	D.	2004/0161636	8/19/2004	Hujanen et al.	428	692	2/17/04
<input type="checkbox"/>	E.	6794287	9/21/2004	Saanila et al.	438	674	3/20/03
<input type="checkbox"/>	F.	6800173	10/5/2004	Chiang et al.	156	345.33	7/9/01
<input type="checkbox"/>	G.	6800552	10/5/2004	Elers et al.	438	680	8/17/02
<input type="checkbox"/>	H.	2004/0202786	10/14/2004	Wongsenakhum et al.	427	250	3/31/04
<input type="checkbox"/>	I.	6811814	11/2/2004	Chen et al.	427	248.1	1/16/02
<input type="checkbox"/>	J.	6818067	11/18/2004	Doering et al.	118	715	4/15/02
<input checked="" type="checkbox"/>	K.	6821889	11/23/2004	Elers et al.	438	680	7/30/02

  

FOREIGN PATENT DOCUMENTS							
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						YES	NO
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NON-PATENT DOCUMENTS - DOCUMENT (Including Author, Title, Source, and Pertinent Pages)				
<input checked="" type="checkbox"/>	M.	Pakrad, C.D., "Pure Tech: Growth of MR/GMR Head Materials," World-wide web, puretechinc.com/tech_papers/tech_papers-4.htm, pp. 1-2		1999
<input type="checkbox"/>	N.	Riihela et al., "Low Temperature Deposition of AlN Films by an Alternate Syppy of Trimethyl Aluminum and Ammonia" Chemical Vapor Deposition, 2 (6): pp. 277-283.		1996
<input type="checkbox"/>	O.	Suntola, Tuomo; Handbook of Crystal Growth, vol. 3, Thin Films and Epitaxy, Part B: Growth Mechanisms and Dynamics, Chapter 14, pp. 601-663, Hurler, ed. Elsevier Science B.V.		1994
<input type="checkbox"/>	P.	Ritala et al., "Atomic Layer Epitaxy-a Valuable Tool for Nanotechnology?" Nanotechnology vol. 10, pages 19-24		1999
<input type="checkbox"/>	Q.	Wang, Shan X., "Advanced Materials for Extremely High Density Magnetic Recording Heads," Department of Electrical Engineering, Stanford University, Stanford, CA 94305-4045, presentation.		no date available
<input type="checkbox"/>	R.	World-wide web, megahaus.com/tech/westerndigital/shitepapers/gmr_wp.shtml, "GMR Head Technology: Increased Areal Density and Improved Performance Areal Density," pp. 1-4.		02/2000
<input type="checkbox"/>	S.	World-wide web, semiconductor.net/semiconductor/issues/issues/1998/feb98/docs/emerging.asp, "GMR Read-Write Heads Yield Data Storage Record," pp. 1-2.		02/1998
<input type="checkbox"/>	T.	World-wide web, stoner.leeds.ac.uk/research/gmr.htm, "Giant Magnetoresistance (GMR) Heads", pp. 1-6.		Printed 02/04/2002
<input type="checkbox"/>	U.	World-wide web, pcgilde.com/ref/hdd/op/heads/techGMR-c.html, "Giant Magnetoresistive (GMR) Heads", pp. 1-4.		Printed 12/18/2004
<input type="checkbox"/>	A.	Utrianen, et al., "Studies of Metallic Film Growth in an Atomic Layer Epitaxy reactor Using M(acac) <sub>2</sub> (M=Ni, Cu, Pt) Precursors", Applied Surface Science, vol. 157, pp. 151-158.		2000
<input checked="" type="checkbox"/>	V.	Ueno et al., "Cleaning of CHF <sub>3</sub> , plasma-etched SiO <sub>2</sub> /SiN/Cu via Structures Using a Hydrogen Plasma, an Oxygen Plasma and Hexafluoroacetylacetone Vapors," J. Vac. Sci. Technology B, vol. 16, No. 6, pp. 2986-2995.		Nov/Dec. 1998

  

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	2/16/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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<b>U.S. PATENT DOCUMENTS</b>							
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<input checked="" type="checkbox"/>	A.	5647911	Vanell et al.	118	715	12/14/93	
<input checked="" type="checkbox"/>	B.	5711811	Suntola et al.	118	711	11/28/95	
<input checked="" type="checkbox"/>	C.	5916369	Anderson et al.	118	715	06/07/95	
<input checked="" type="checkbox"/>	D.	2003/0003635 A1	Paranjpe et al.	438	149	05/23/01	
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<b>NON-PATENT DOCUMENTS - DOCUMENT (Including Author, Title, Source, and Pertinent Pages)</b>							
<input checked="" type="checkbox"/>	L.	Omstead, Thomas, et al.; "Filling High-AR Structures Using Pulsed Nucleation Layer Deposition", Solid State Technology, Vol. 45, pp. 51-56.					09/2002
<input type="checkbox"/>	M.						
<input type="checkbox"/>	N.						
<input type="checkbox"/>	O.						
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<input type="checkbox"/>	U.						
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EXAMINER				DATE CONSIDERED <b>2/18/02</b>			
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